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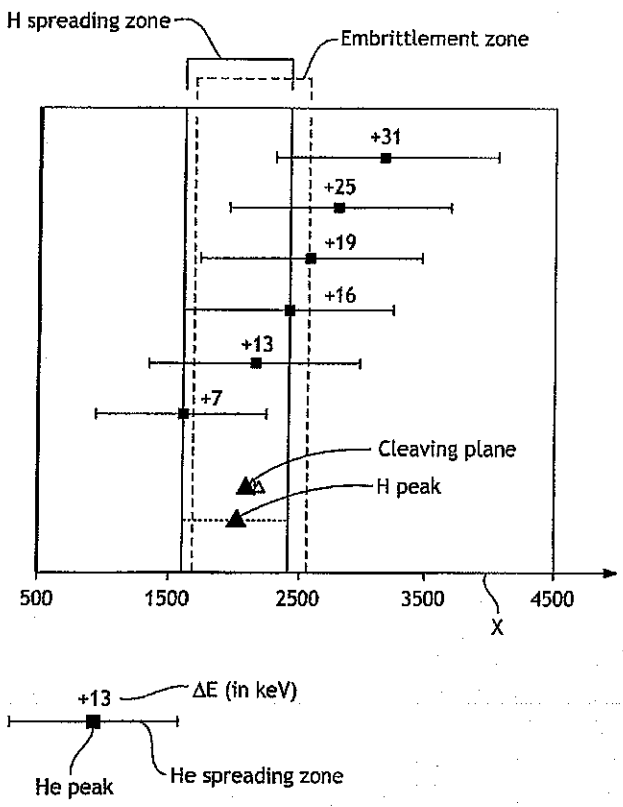
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(54) Title: THIN LAYER TRANSFER METHOD WHEREIN A CO-IMPLANTATION STEP IS PERFORMED ACCORDING TO CONDITIONS AVAOIDING BLISTERS FORMATION AND LIMITING ROUGHNESS



(57) Abstract: The invention proposes a method for transferring a thin layer wherein a co-implantation step of two different species is performed. The implantation energies of said first and second species are selected such that said second species peak is located in the thickness of the donor substrate within said embrittlement zone and more in-depth than said first species spreading zone, and the implantation doses of said first and second species are selected to be substantially similar, the first species implantation dose counting from 40% to 60% of the total implantation dose.

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